Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A method of forming a thin film pattern by placing a functional liquid on a substrate, comprising:

a bank formation step of forming banks in accordance with the thin film pattern on the substrate;

a residue processing step of removing residue between the banks; and

a material placement step of placing the functional liquid between the banks removed the residue.

2. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step comprises a step of removing residue in bottom portions between the banks.

3. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step comprises a photo irradiation processing step.

4. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step comprises a plasma processing step that uses a predetermined processing gas.

5. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step comprises a plasma processing step that uses a predetermined processing gas and a photo irradiation processing step.

6. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step performs etching using acid.

7. (Original) A method of forming a thin film pattern according to claim 4, wherein the banks are formed so as to extend in a predetermined direction, and

the plasma processing step supplies the processing gas while relatively moving the substrate in the predetermined direction relative to the processing gas.

8. (Original) A method of forming a thin film pattern according to claim 5, wherein the banks are formed so as to extend in a predetermined direction, and

the plasma processing step supplies the processing gas while relatively moving the substrate in the predetermined direction relative to the processing gas.

9. (Original) A method of forming a thin film pattern according to claim 1, further comprising a repellency processing step of imparting repellency to the banks after the residue processing step.

10. (Original) A method of forming a thin film pattern according to claim 9, further comprising a step of removing residue from bottom portions between the banks after the repellency processing step of imparting repellency to the banks.

11. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a step of removing residue from bottom portions between the banks.

12. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a photo irradiation processing step.

13. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a plasma processing step that uses a predetermined processing gas.

14. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a plasma processing step that uses a predetermined processing gas and a photo irradiation processing step.

15. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step performs etching using acid.

16. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step is performed once again after the material placement step.

17. (Original) A method of forming a thin film pattern according to claim 1, wherein the functional liquid exhibits electroconductivity after undergoing heat processing or light processing.

18. (Original) A method of forming a thin film pattern according to claim 1, wherein the functional liquid contains electroconductive fine particles.

19. (Original) A device manufacturing method comprising a step of forming a thin film pattern on the substrate using the method of forming a thin film pattern according to claim 1.

20. (Original) An electro-optical apparatus comprising a device manufactured using the device manufacturing method according to claim 19.

21. (Original) An electronic apparatus comprising the electro-optical apparatus according to claim 20.

22. (Currently Amended) A method of manufacturing an active matrix substrate comprising:

a first step of forming a gate wire on a substrate;

a second step of forming a gate insulating film on the gate wire;

a third step of laminating a semiconductor layer via the gate insulating film;

a fourth step of forming a source electrode and drain electrode on the gate insulating film;

a fifth step of placing a non-conductive material on the source electrode and the drain electrode;

a sixth step of forming a pixel electrode after the placement of the insulating material,

wherein at least one of the first, fourth, and sixth steps further comprising:

a bank forming step of forming banks to correspond to a formation pattern;

a residue processing step of removing residue between the banks; and

a material placement step of placing a ~~the~~ functional material between the banks removed the residue by being discharged using a droplet discharge apparatus.